Central™
Semiconductor Corp.

PROCESS CPD41

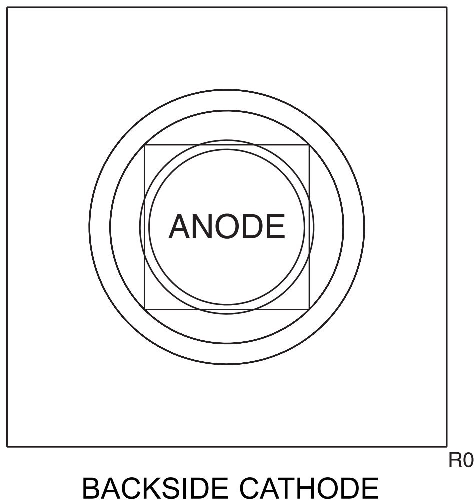
Switching Diode

High Current Switching Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER
29,250

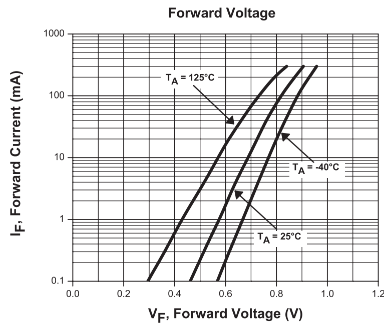
PRINCIPAL DEVICE TYPES
1N3600
1N4150
CMPD4150

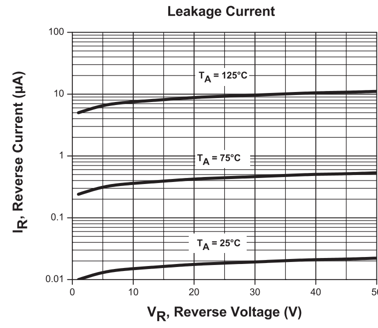
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

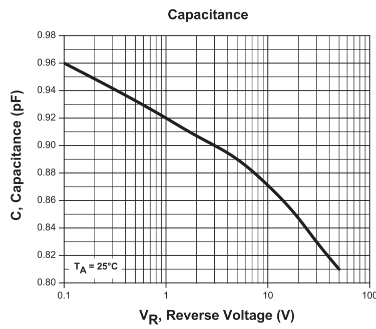
R3 (25-August 2006)

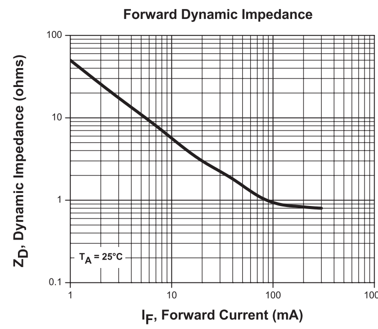
PROCESS CPD41

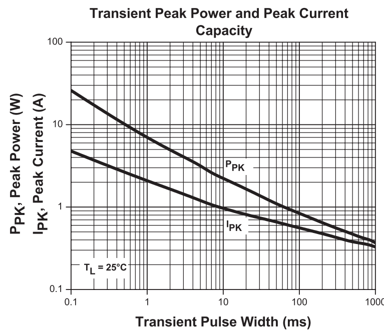
Typical Electrical Characteristics

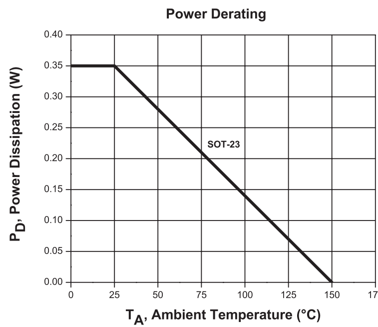












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